

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF75-28S** is Designed for bradband applications up to 30 MHz.

FEATURES:

- $P_G = 18$ dB min. at 75 W/30 MHz
- $IMD_3 = -30$ dBc max. at 75 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	166 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.05 °C/W

PACKAGE STYLE .380 STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10607

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10$ Ω	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			80	pF
P_G IMD_3	$V_{CE} = 28$ V $I_{CQ} = 75$ mA $f = 30$ MHz $P_{OUT} = 75$ W	13.5	14.5	-30	dB dBc